

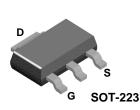
# **FQT5P10** P-Channel QFET<sup>®</sup> MOSFET -100 V, -1.0 A, 1.05 Ω

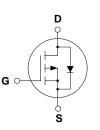
### Description

This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor®'s proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

### Features

- -1.0 A, -100 V,  $R_{DS(on)}\text{=}1.05~\Omega(Max.)$  @V\_{GS}\text{=-10 V, }I\_{D}\text{=-0.5 A}
- Low Gate Charge (Typ. 6.3 nC)
- Low Crss (Typ. 18 pF)
- 100% Avalanche Tested





### Absolute Maximum Ratings T<sub>c</sub> = 25°C unless otherwise noted

Symbol	Parameter		FQT5P10	Unit
V <sub>DSS</sub>	Drain-Source Voltage		-100	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°	°C)	-1.0	А
	- Continuous (T <sub>C</sub> = 70°C)		-0.8	А
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	-4.0	А
V <sub>GSS</sub>	Gate-Source Voltage		± 30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	55	mJ
I <sub>AR</sub>	Avalanche Current	(Note 1)	-1.0	А
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	0.2	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	-6.0	V/ns
P <sub>D</sub>	Power Dissipation ( $T_C = 25^{\circ}C$ )		2.0	W
	- Derate above 25°C		0.016	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C
Τ <sub>L</sub>	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

## **Thermal Characteristics**

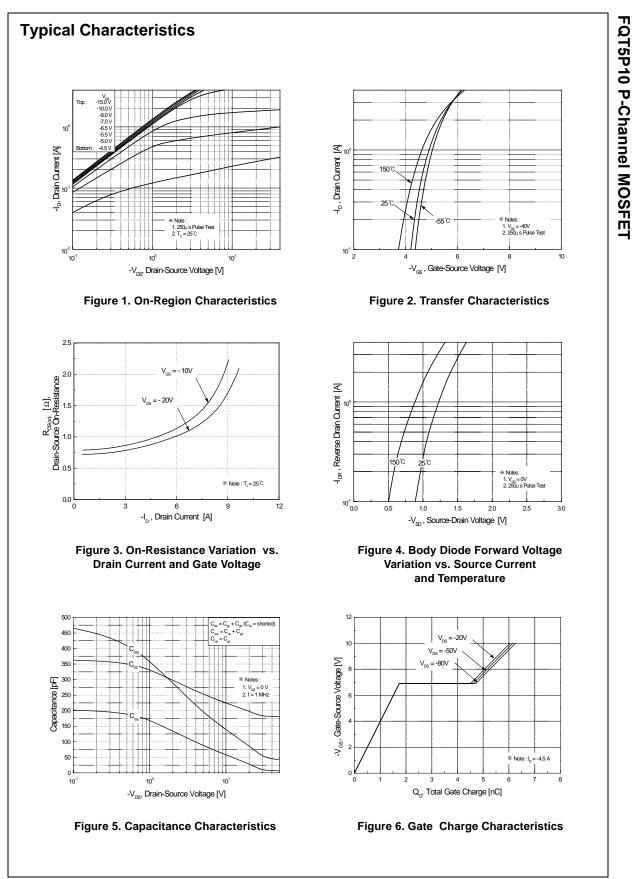
Parameter	Тур	Max	Unit
nermal Resistance, Junction-to-Ambient *		62.5	°C/W
		ermal Resistance, Junction-to-Ambient *	ermal Resistance, Junction-to-Ambient * 62.5



March 2013

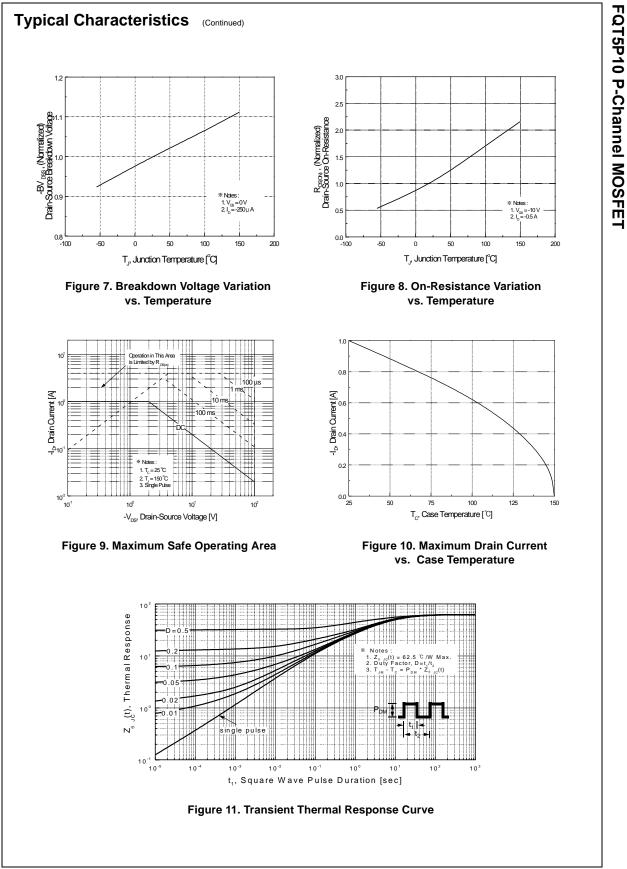
Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	racteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = -250 μA	-100			V
ΔB <sub>VDSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D = -250 \ \mu A$ , Referenced to 2	25°C	-0.1		V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = -100 V, V <sub>GS</sub> = 0 V			-1	μA
		$V_{DS} = -80 \text{ V}, \text{ T}_{C} = 125^{\circ}\text{C}$			-10	μΑ
GSSF	Gate-Body Leakage Current, Forward	$V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
GSSR	Gate-Body Leakage Current, Reverse	$V_{GS} = 30 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$			100	nA
On Cha	racteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-2.0		-4.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -0.5 A		0.82	1.05	Ω
Ĵfs	Forward Transconductance	$V_{DS} = -40 \text{ V}, \text{ I}_{D} = -0.5 \text{ A}$ (No	ote 4)	1.4		S
Dunom			·			
C <sub>iss</sub>	ic Characteristics Input Capacitance	N/ 05 Y/ Y/ 0 Y/		190	250	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = -25 V, V <sub>GS</sub> = 0 V, f = 1.0 MHz		70	90	pF
S <sub>rss</sub>	Reverse Transfer Capacitance	1 = 1.0 MHz		18	25	pF
d(on) r	Turn-On Delay Time Turn-On Rise Time	$V_{DD} = -50 \text{ V}, \text{ I}_{D} = -4.5 \text{ A},$		9 70	30 150	ns ns
r		$R_{G} = 25 \Omega$				ns
d(off)	Turn-Off Delay Time	(Not	e 4, 5)	12	35	ns
f C	Turn-Off Fall Time			30	70	ns
כ <sup>מ</sup>	Total Gate Charge	$V_{DS} = -80 \text{ V}, \text{ I}_{D} = -4.5 \text{ A},$		6.3	8.2	nC
Q <sub>gs</sub>	Gate-Source Charge	$V_{GS} = -10 V$		1.7		nC
ସୁ <sub>gd</sub>	Gate-Drain Charge	(100	e 4, 5)	3.0		nC
	ource Diode Characteristics a	V			1.0	
S	Maximum Continuous Drain-Source Did				-1.0	A
SM	Maximum Pulsed Drain-Source Diode F				-4.0	A
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	$V_{GS} = 0 V, I_S = -1.0 A$ $V_{GS} = 0 V, I_S = -4.5 A,$			-4.0	V
trr Orr	Reverse Recovery Time		 ote 4)	85 0.27		ns
Qrr otes:	Reverse Recovery Charge			0.27		μC
$\begin{array}{l} \mbox{Repetitive R} \\ \mbox{L} = 83mH, \mbox{I}_{SD} \\ \mbox{I}_{SD} \leq -4.5A \\ \mbox{Pulse Test}: \end{array}$	ating : Pulse width limited by maximum junction temper $_{AS}$ = -1.0A, $V_{DD}$ = -25V, $R_G$ = 25 $\Omega$ , Starting $T_J$ = 25°C , di/dt $\leq$ 300A/us, $V_{DD}$ $\leq$ BV <sub>DSS</sub> , Starting $T_J$ = 25°C Pulse width $\leq$ 300µs, Duty cycle $\leq$ 2% independent of operating temperature	rature				

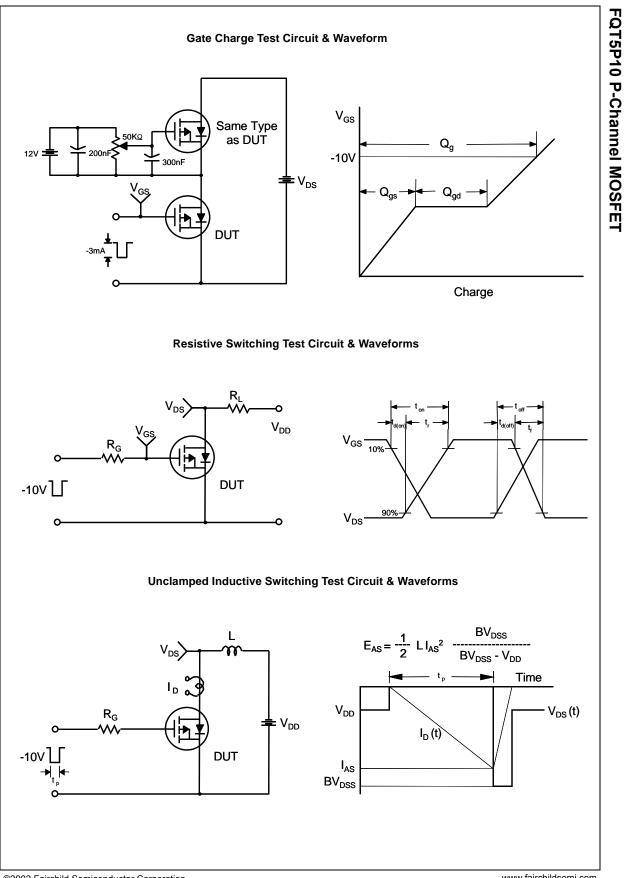
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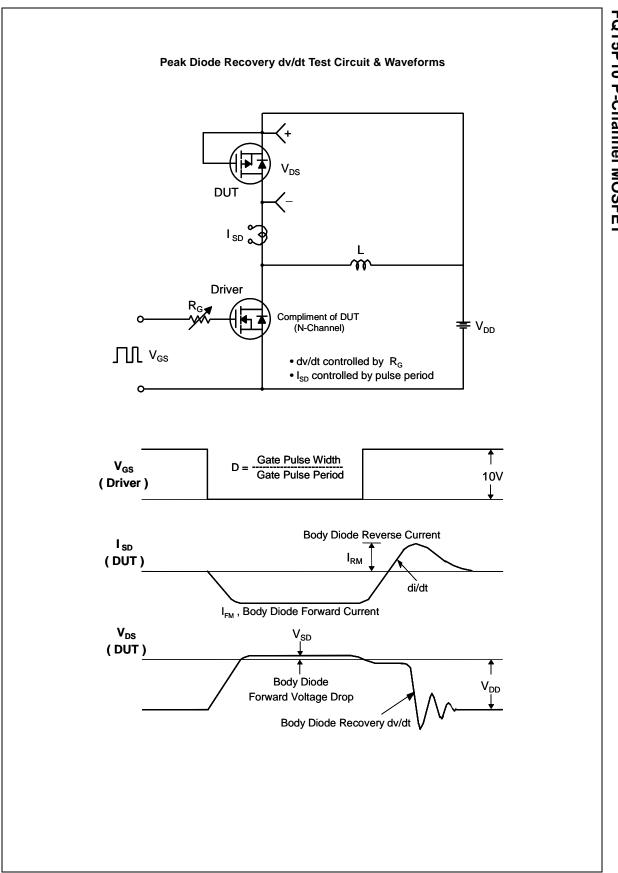
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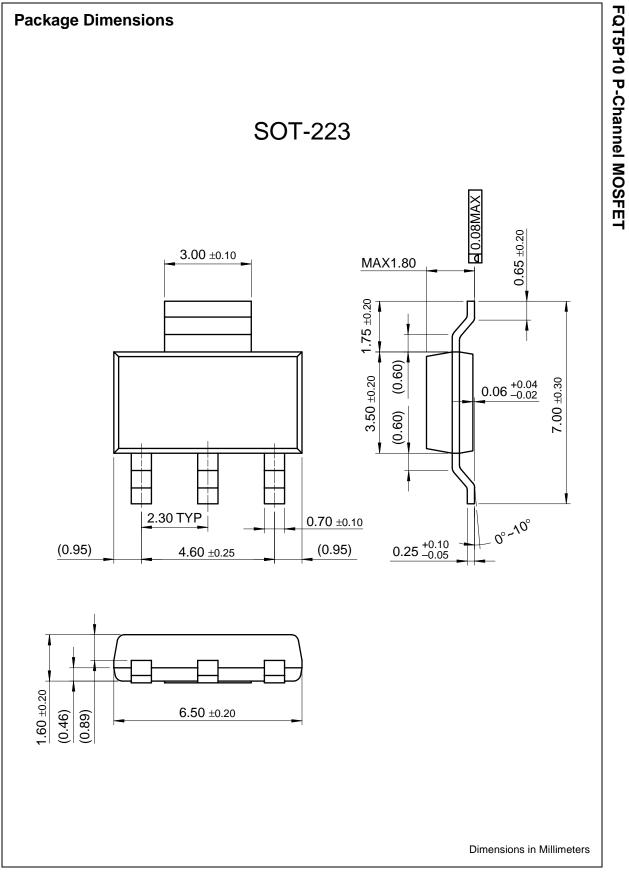




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